

General Description

- Latest Trench Power AlphaMOS (α MOS LV) technology
- Integrated Schottky Diode (SRFET)
- Very Low $R_{DS(on)}$ at 4.5V_{GS}
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

Application

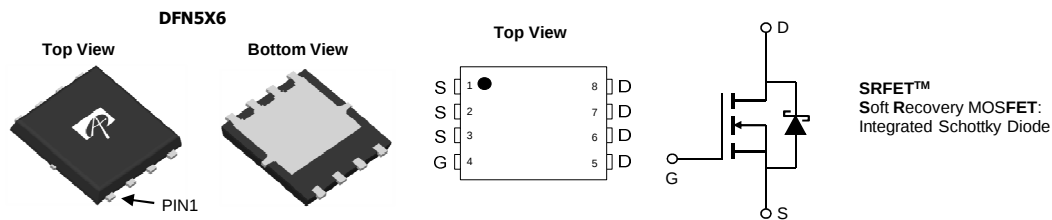
- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	32A
$R_{DS(on)}$ (at $V_{GS}=10V$)	< 3.6m Ω
$R_{DS(on)}$ (at $V_{GS} = 4.5V$)	< 5m Ω

100% UIS Tested

100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current ^G	T _C =25℃	I _D	32	A
	T _C =100℃		25	
Pulsed Drain Current ^C		I _{DM}	128	
Continuous Drain Current	T _A =25℃	I _{DSM}	27	A
	T _A =70℃		21	
Avalanche Current ^C		I _{AS}	50	A
Avalanche energy L=0.05mH ^C		E _{AS}	63	mJ
V _{DS} Spike	100ns	V _{SPIKE}	36	V
Power Dissipation ^B	T _C =25℃	P _D	41	W
	T _C =100℃		16	
Power Dissipation ^A	T _A =25℃	P _{DSM}	4.1	W
	T _A =70℃		2.6	
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	℃

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	24	30	$^\circ\text{C/W}$
$t \leq 10\text{s}$				
Maximum Junction-to-Ambient ^{A D}	$R_{\theta JC}$	53	64	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Case		2.6	3	$^\circ\text{C/W}$
Steady-State				

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =10mA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =125°C			0.5 100	mA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.4	1.8	2.4	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		3 3.9	3.6 4.7	mΩ
		V _{GS} =4.5V, I _D =20A		3.9	5	mΩ
				85		S
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A				
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.48	0.6	V
I _S	Maximum Body-Diode Continuous Current ⁶				32	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		1975		pF
C _{oss}	Output Capacitance			913		pF
C _{rss}	Reverse Transfer Capacitance			92		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.7	1.5	2.3	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A		29.0	40	nC
Q _g (4.5V)	Total Gate Charge			13.6	19	nC
Q _{gs}	Gate Source Charge			5.8		nC
Q _{gd}	Gate Drain Charge			5.3		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		7.9		ns
t _r	Turn-On Rise Time			4.0		ns
t _{D(off)}	Turn-Off DelayTime			27.3		ns
t _f	Turn-Off Fall Time			6.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=500A/μs		19		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=500A/μs		36.7		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

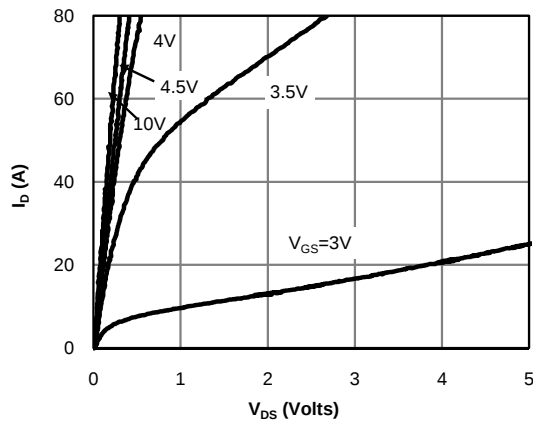


Fig 1: On-Region Characteristics (Note E)

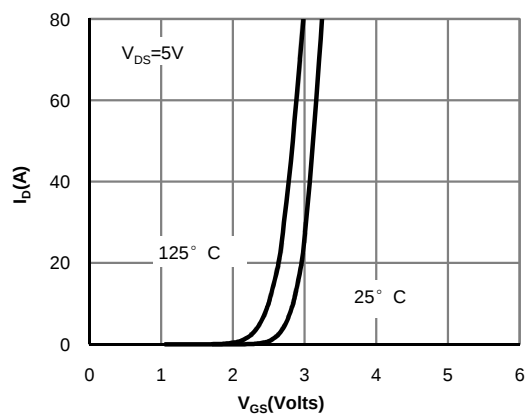


Figure 2: Transfer Characteristics (Note E)

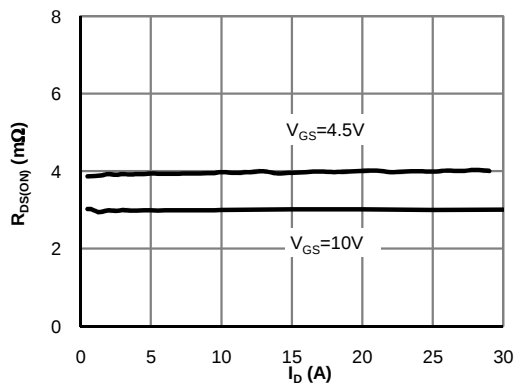


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

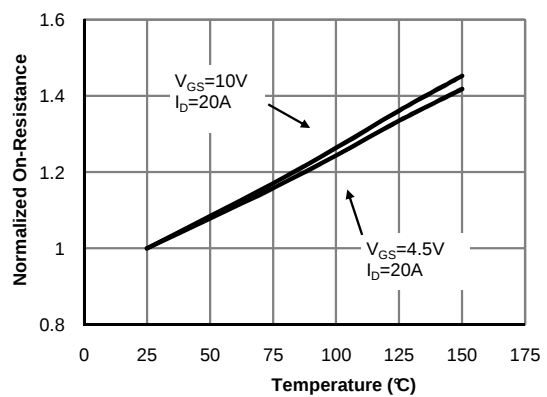


Figure 4: On-Resistance vs. Junction Temperature (Note E)

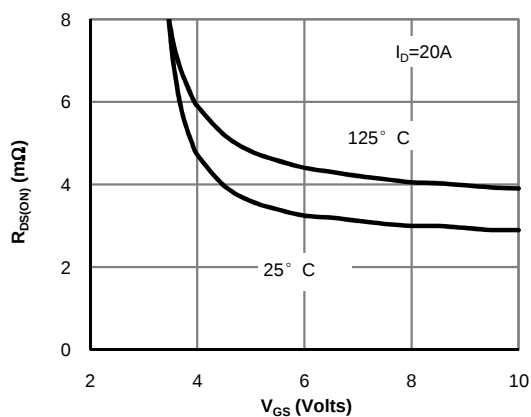


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

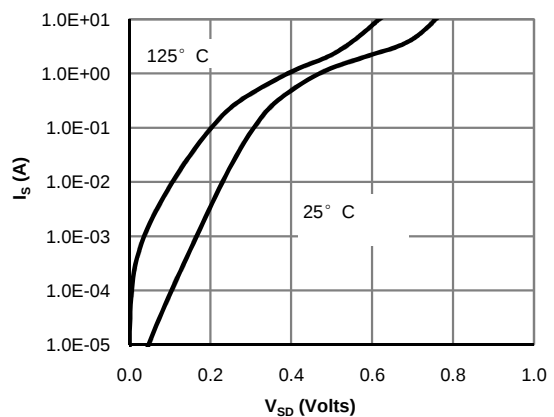
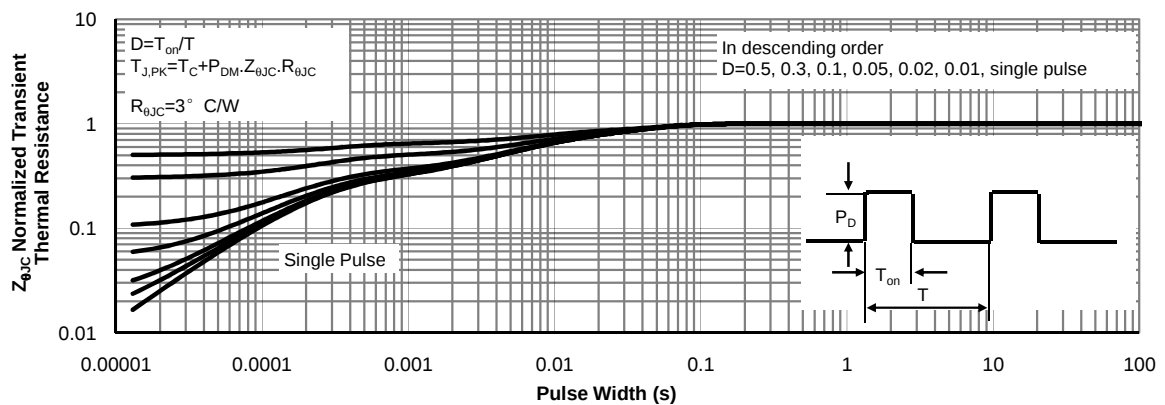
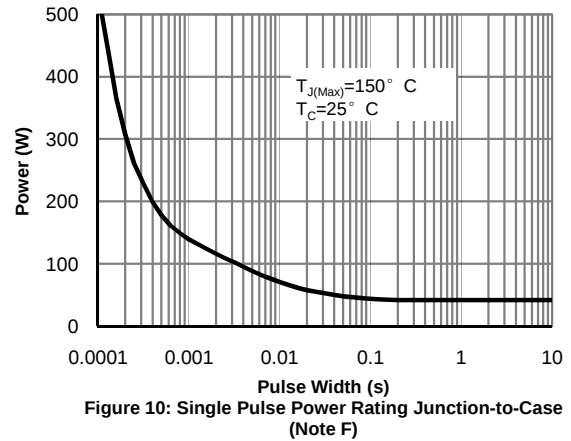
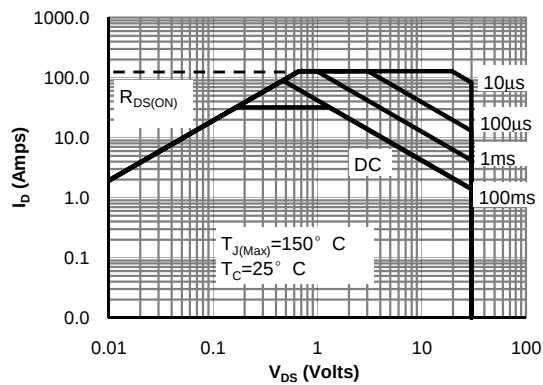
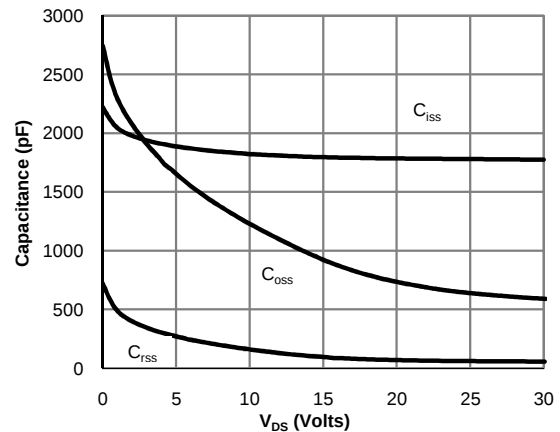
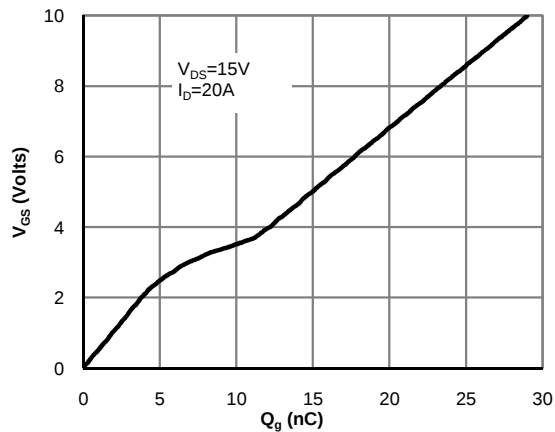


Figure 6: Body-Diode Characteristics (Note E)

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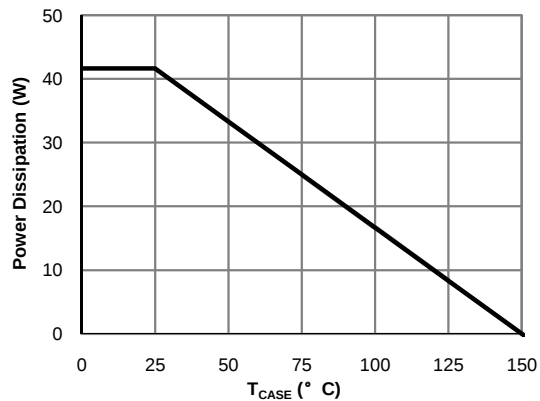


Figure 12: Power De-rating (Note F)

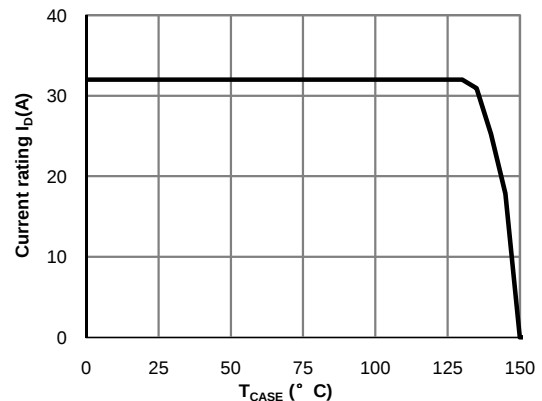


Figure 13: Current De-rating (Note F)



Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

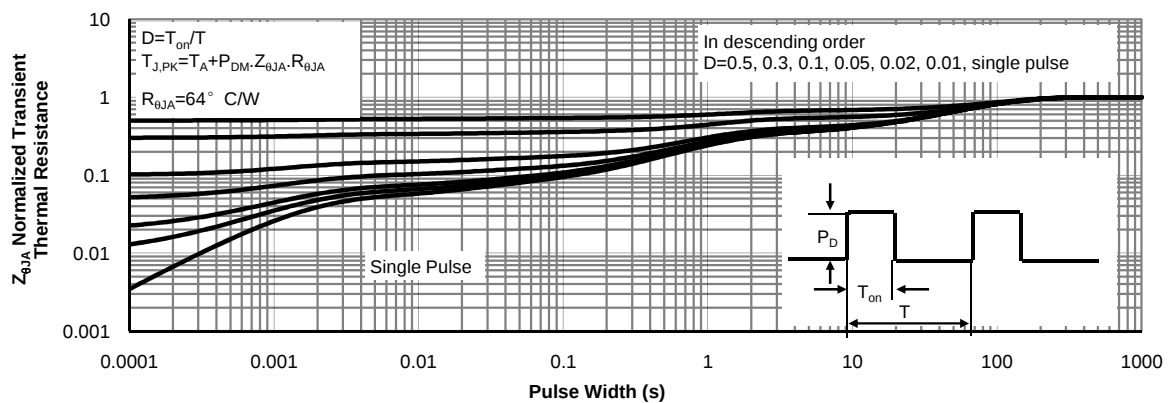
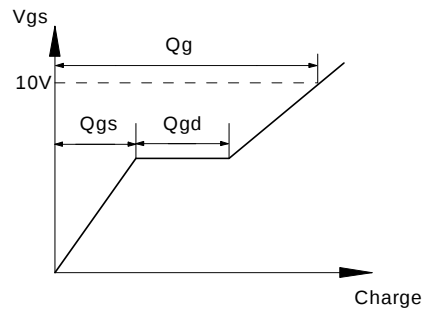
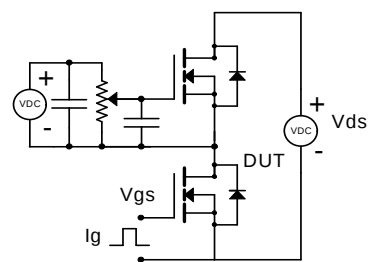
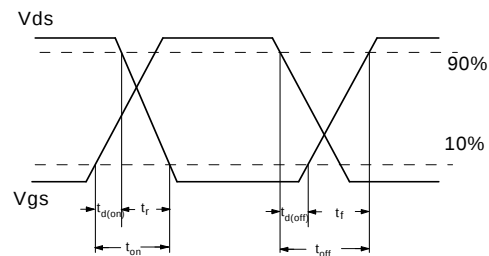
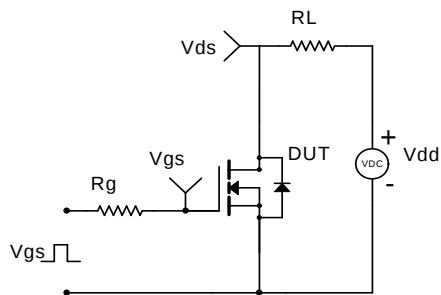


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

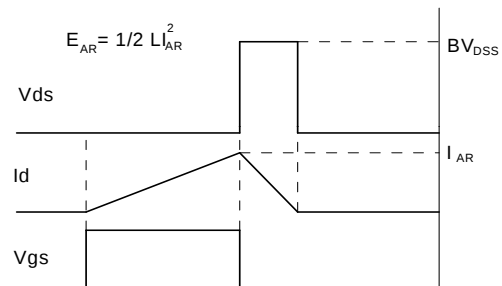
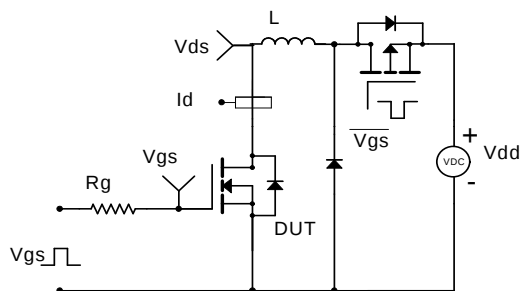
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

